

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

SHIOYA et al

Serial No.:

Filed: November 20, 2001

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the captioned application as follows:

IN THE CLAIMS:

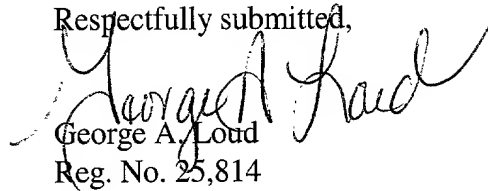
Please rewrite claim 12, 13 and 25 as follows:

12. (Amended) A semiconductor device manufacturing method according to claim 8, wherein the interlayer insulating film is any one of an FSG film and a porous SiO₂ film.

13. (Amended) A semiconductor device manufacturing method according to claim 6, wherein the silicon-containing insulating film is any one selected from the group consisting of an SiOCH film, an SiO film, an SiN film, an SiONCH film, an SiCH film, and an SiCNH film.

25. (Amended) A semiconductor device manufactured by the semiconductor device manufacturing method set forth in claim 1.

Respectfully submitted,


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Dated: November 20, 2001

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12. (Amended) A semiconductor device manufacturing method according to claim 8 [or claim 11], wherein the interlayer insulating film is any one of an FSG film and a porous SiO₂ film.

13. (Amended) A semiconductor device manufacturing method according to claim 6 [or claim 9], wherein the silicon-containing insulating film is any one selected from the group consisting of an SiOCH film, an SiO film, an SiN film, an SiONCH film, an SiCH film, and an SiCNH film.

25. (Amended) A semiconductor device manufactured by the semiconductor device manufacturing method set forth in claim 1 [any one of claims 1, 4, and 9].

10021-6933650